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			ι	I.S. PATENT DOCUME	NTS				
Examiner Initials*	Cite No. ¹		ment ind Code ² known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY		Pages, Colu Where Relevan Relevant Fig	Passages o	
SAV		5798027		Lefebvre et al	8/25/1998		254	192 0	
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Examiner Cite Foreign Patent Document Initials* No.¹ Office³ Number⁴ Kind Code⁵ (if known)		REIGN PATENT DOCU Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document Relev		, Columns, Lines, ant Passages or ant Figures Appea	•			
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		OTHER PRIOR	ART - NON PATENT LITERATURI	DOCUMENTS			
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
SHV		Broughton J.N. et al	Long Throw Sputter Deposition of Titanium at Low Pressures	1995 VMIC Conference June 27-29 1995 ISMIC – 104/95/0201 (pages 201- 203)			
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SHV		A. Belkind et al	Electrical Dynamics of Pulsed Plasmas	1998 Society of Vacuum Coaters 505 pages 321-326			
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Application Number 10/643,556

Filing Date August 18, 2003

First Named Inventor Jesse D. Wolfe et al

Group Art Unit /753

Examiner Name Ver Steecy

Attorney Docket Number IL-11072

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SHV		WO	01/98553	A1/	Vladimir,	Kouznetsov	12-27-2001	CJ3C	14/.35		
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